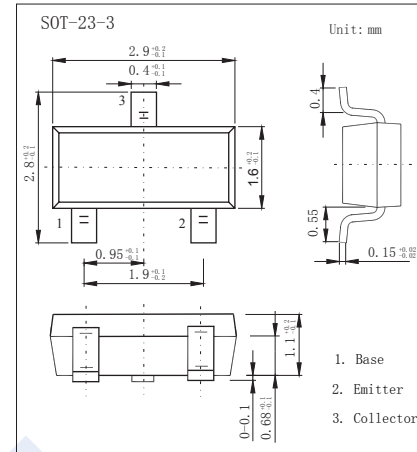


PNP Transistors

2SA1484-HF

■ Features

- Collector Current Capability $I_C=100\text{mA}$
- Collector Emitter Voltage $V_{CE0}=-90\text{V}$
- Pb-Free Package May be Available. The G-Suffix Denotes a Pb-Free Lead Finish



■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector to base voltage	V_{CB0}	-90	V
Collector to emitter voltage	V_{CE0}	-90	V
Emitter to base voltage	V_{EB0}	-5	V
Collector current	I_C	-100	mA
Collector power dissipation	P_C	150	mW
Junction temperature	T_j	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +150	$^\circ\text{C}$

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector to base breakdown voltage	$V_{(BR)CBO}$	$I_C = -10\ \mu\text{A}, I_E = 0$	-90			V
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = -1\ \text{mA}, R_{BE} = \infty$	-90			V
Emitter to base breakdown voltage	$V_{(BR)EBO}$	$I_E = -10\ \mu\text{A}, I_C = 0$	-5			V
Collector cutoff current	I_{CBO}	$V_{CB} = -70\ \text{V}, I_E = 0$			-0.1	μA
Emitter cutoff current	I_{EBO}	$V_{EB} = -4\ \text{V}, I_C = 0$			-0.1	μA
DC current transfer ratio	h_{FE}	$V_{CE} = -12\ \text{V}, I_C = -2\ \text{mA} (*)$	250		800	
Collector to emitter saturation voltage	$V_{CE(sat)}$	$I_C = -10\ \text{mA}, I_B = -1\ \text{mA} (*)$			-0.15	V
Base to emitter saturation voltage	$V_{BE(sat)}$	$I_C = -10\ \text{mA}, I_B = -1\ \text{mA} (*)$			-1	V

* Pulse test.

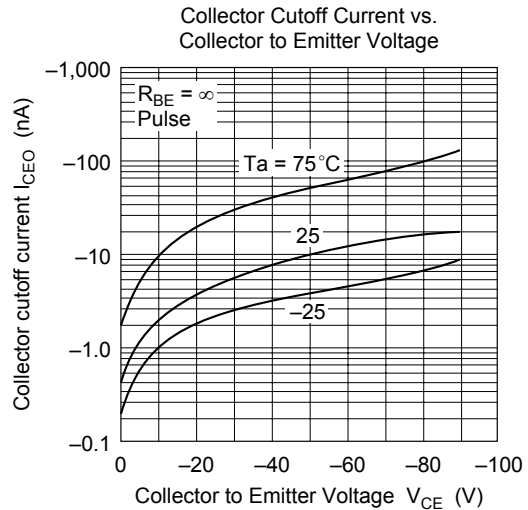
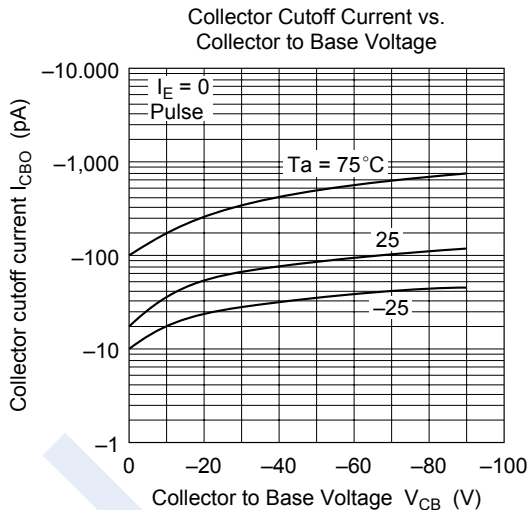
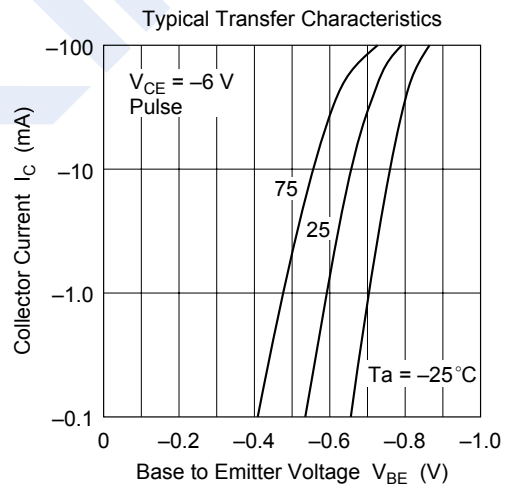
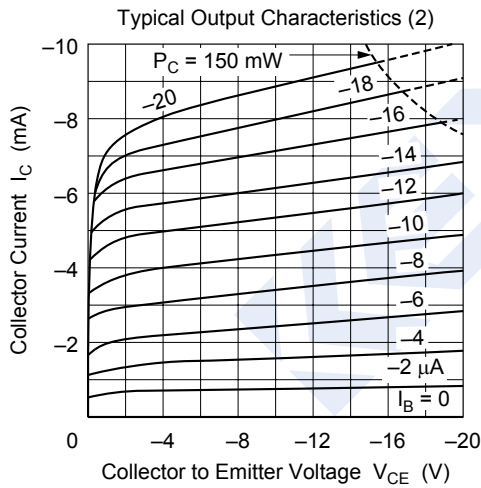
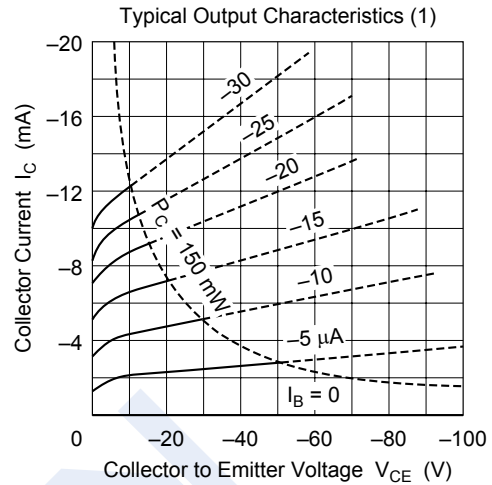
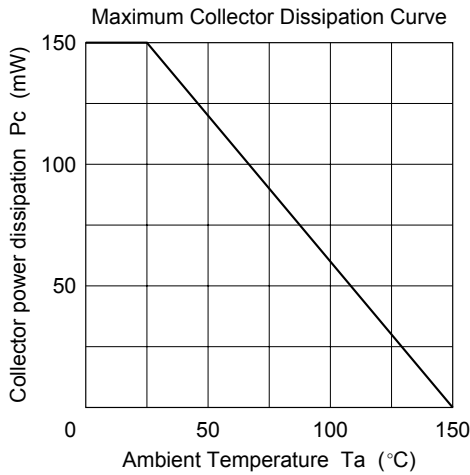
■ Classification of h_{FE}

Type	2SA1484-D-HF	2SA1484-E-HF
Range	250-500	400-800
Marking	IRD _F	IRE _F

PNP Transistors

2SA1484-HF

■ Typical Characteristics



PNP Transistors

2SA1484-HF

■ Typical Characteristics

